

TECHNICAL DATA
DATASHEET 4963, Rev. A.1

# SILICON SCHOTTKY RECTIFIER DIE Low Forward Voltage Drop (200 °C T<sub>J</sub> Operation)

## **Applications:**

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

#### Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

## **Maximum Ratings**(1):

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	150	V
Max. Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle, rectangular wave form	7.5	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave (1)	140	А
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C}, \ I_{AS} = 2.0  \text{A}, \\ L = 6.5  \text{mH}$	13.0	mJ
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 $\mu$ s $f$ limited by $T_J$ max $V_A$ =1.5 $V_R$	2.0	А
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +200	°C

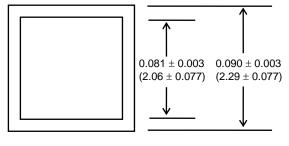
#### Electrical Characteristics(1):

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 7.5A, Pulse, T <sub>J</sub> = 25 °C	0.89	V
	$V_{F2}$	@ 7.5A, Pulse, T <sub>J</sub> = 125 °C	0.74	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 150V, Pulse,	0.25	mA
		T <sub>J</sub> = 25 °C		
	$I_{R2}$	@V <sub>R</sub> = 150V, Pulse,	4.0	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	C <sub>T</sub>	$@V_R = 5V, T_C = 25  ^{\circ}C$	250	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

(1) in SHD package

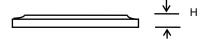
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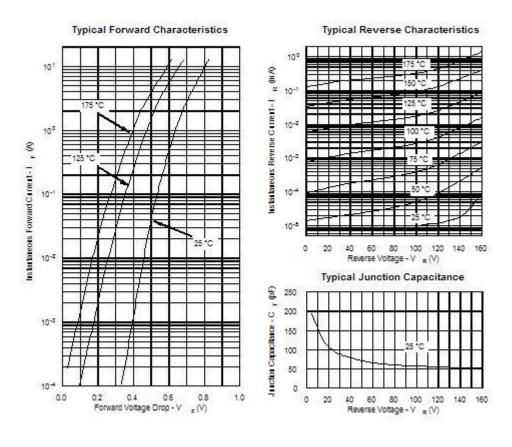
#### Mechanical Dimensions: In Inches / mm



Bottom side metalization Ti/Ni/Ag - 5 kÅ Ag minimum. Top side metalization Ti/Al - 25 kÅ Al or Ti/Ni/Ag - 30 kÅ Ag Bottom side is cathode, top side is anode. Dimension H =  $0.0105 \pm 0.001$  ( $0.27 \pm 0.026$ ) for Al top;

Dimension H =  $0.0155 \pm 0.001$  (0.39  $\pm 0.026$ ) for Ag top.





### SD090SC150A/B/C

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